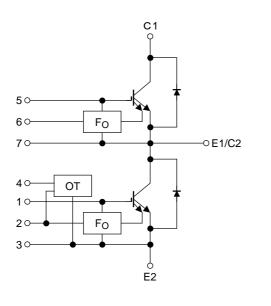
TOSHIBA IGBT Module Silicon N Channel IGBT

MG400J2YS60A(600V/400A 2in1)

High Power Switching Applications Motor Control Applications

- Integrates a complete half bridge power circuit and fault-signal output circuit in one package. (short circuit and over temperature)
- The electrodes are isolated from case.
- Low thermal resistance
- VCE (sat) = 1.8 V (typ.)

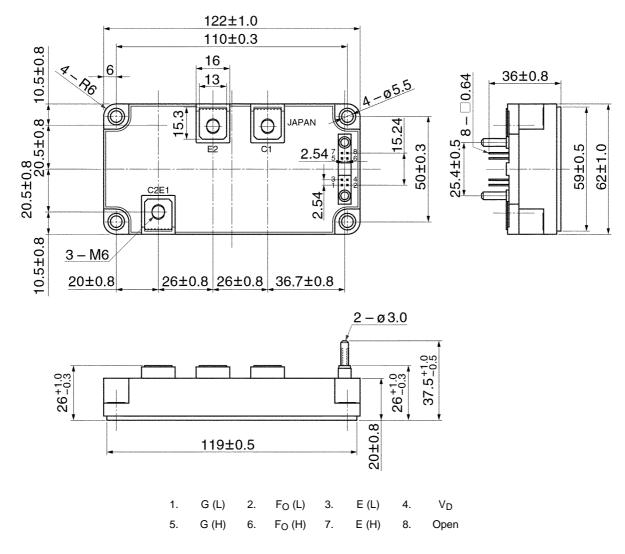
Equivalent Circuit



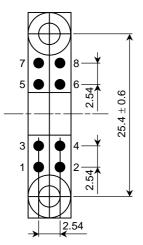
Signa	al terminal						
1.	G (L)	2.	F _O (L)	3.	E (L)	4.	V_{D}
5.	G (H)	6.	F _O (H)	7.	E (H)	8.	Open

Package Dimensions: 2-123C1B

Unit: mm



Signal Terminal Layout



4		2		2		4	\/-
1.	G (L)	Ζ.	F _O (L)	з.	E (L)	4.	۷D
5.	G (H)	6.	F _O (H)	7.	E (H)	8.	Open

Weight: 375 g

Maximum Ratings (Ta = 25°C)

Stage	Characteristics		Symbol	Rating	Unit	
	Collector-emitter voltage	V _{CES}	600	V		
	Gate-emitter voltage	V _{GES}	±20	V		
	Collector current	DC	I _C 400		٨	
Inverter		1 ms	I _{CP}	800	A	
	Forward current	DC	١ _F	400	А	
	Forward current	1 ms	I _{FM}	800	A	
	Collector power dissipation (Tc =	25°C)	P _C	2160	W	
	Control voltage (OT)	VD	20	V		
Inverter Control Module	Fault input voltage	VFO	20	V		
	Fault input current		IFO	20	mA	
	Junction temperature	Тј	150	°C		
	$\begin{tabular}{ c c c c c c c } \hline Collector power dissipation (Tc = 25°C) & P_C & 2160 \\ \hline Control voltage (OT) & V_D & 20 \\ \hline Fault input voltage & VF_O & 20 \\ \hline Fault input current & IF_O & 20 \\ \hline Fault input current & IF_O & 20 \\ \hline Junction temperature & T_j & 150 \\ \hline Storage temperature range & T_{stg} & -40~125 \\ \hline \end{tabular}$	°C				
Module	Operation temperature range	T _{ope}	-20~100	°C		
	Isolation voltage	V _{isol}	2500 (AC 1 min)	V		
	Screw torque	—	3 (M5)	N∙m		

Electrical Characteristics ($T_j = 25^{\circ}C$)

1. Inverter Stage

Characteristics		Symbol	Test Condition		Min	Тур.	Max	Unit
Gate leakage current			$V_{GE} = \pm 20 \text{ V}, \text{ V}_{CE} = 0$		_		+3/-4	mA
		IGES	$V_{GE} = +10 \text{ V}, \text{ V}_{CE} = 0$				100	nA
Collector cut-off current		ICES	$V_{CE} = 600 \text{ V}, \text{ V}_{GE} = 0$				1.0	mA
Gate-emitter cut-off voltage		V _{GE (off)}	$V_{CE} = 5 \text{ V}, \text{ I}_{C} = 400 \text{ mA}$		5.0	6.5	8.0	V
Collector-emitter saturation voltage		V _{CE (sat)}	$V_{GE} = 15 V$,	Tj = 25°C	_	1.8	2.1	V
				Tj = 125°C	_	_	2.3	v
Input capacitance)	C _{ies}	V _{CE} = 10 V, V _{GE} = 0, f = 1 MHz		_	3500	_	pF
	Turn-on delay time	t _{d (on)}		_{CC} = 300 V, I _C = 400 A _{GE} = ±15 V, R _G = 7.5 Ω (Note 1)	0.10	_	1.00	μs
Switching time	Turn-off time	t _{off}			_	_	2.00	
	Fall time	t _f					0.50	
Reverse recovery time		t _{rr}					0.50	
Forward voltage		V _F	I _F = 400 A			1.8	2.2	V

Note 1: Switching time test circuit & timing chart

2. Control (Tc = 25°C)

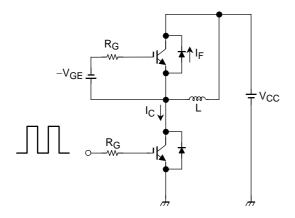
Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Fault output current	OC	$V_{GE} = 15 V$	480	_	_	А
Over temperature	OT	—	100	—	125	°C
Fault output delay time	^t d (Fo)	$V_{CC}=300$ V, $V_{GE}=\pm15$ V	_	—	6.5	μS

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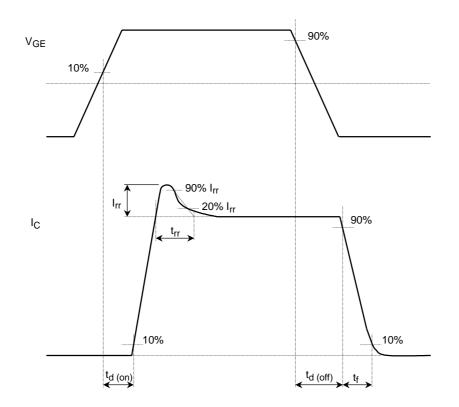
3. Module (Tc = 25° C)

Characteristics Symbol		Test Condition	Min	Тур.	Max	Unit	
Junction to case thermal resistance	Put (1)	Inverter IGBT stage	_	_	0.057 °C/W		
Junction to case thermal resistance	R _{th (j-c)}	Inverter FRD stage	_	_	0.068	0/11	
Case to fin thermal resistance	R _{th (c-f)}	With silicon compound	_	0.013		°C/W	

Switching Time Test Circuit



Timing Chart



Remark

<Short circuit capability condition>

- Short circuit capability is 6 µs after fault output signal. Please keep following condition to use fault output signal.
 - VCC ≤ 375 V
 - $13.8 \text{ V} \le \text{VGE} \le 16.0 \text{ V}$
 - $R_G \ge 7.5 \Omega$
 - $T_j \leq 50^{\circ}C$

<Gate voltage>

• To use this product, VGE must be provided higher than 13.8 V. In case VGE is less than 13.8 V, fault signal FO may not be output even under error conditions.

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